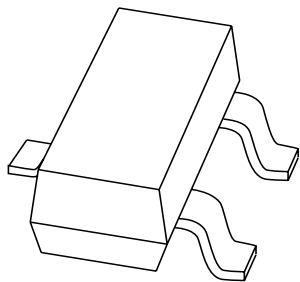


DATA SHEET



BC856; BC857; BC858 PNP general purpose transistors

Product data sheet
Supersedes data of 2003 Apr 09

2004 Jan 16

PNP general purpose transistors

BC856; BC857; BC858

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 65 V).

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

PNP transistor in a SOT23 plastic package.

NPN complements: BC846, BC847 and BC848.

MARKING

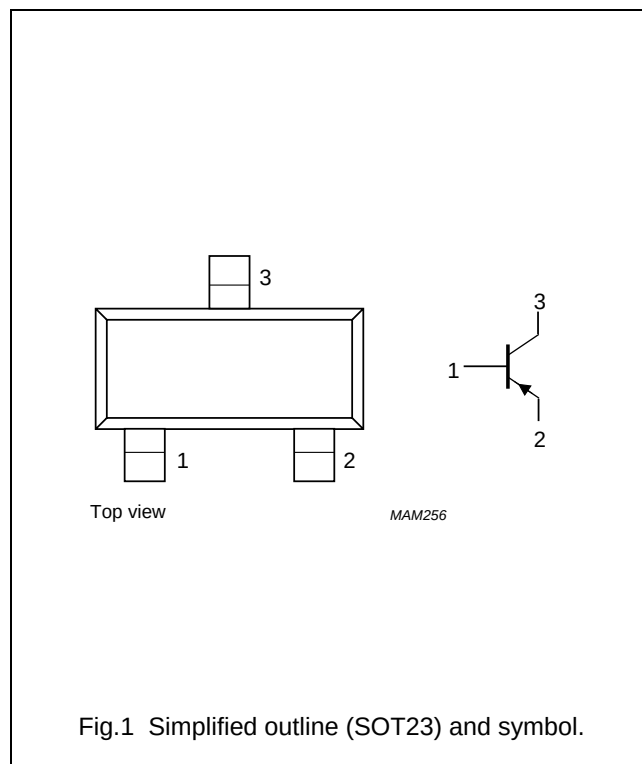
TYPE NUMBER	MARKING CODE ⁽¹⁾
BC856	3D*
BC856A	3A*
BC856B	3B*
BC857	3H*
BC857A	3E*
BC857B	3F*
BC857C	3G*
BC858B	3K*

Note

- * = p: made in Hong Kong.
* = t: made in Malaysia.
* = W: made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BC856	—	plastic surface mounted package; 3 leads	SOT23
BC857	—	plastic surface mounted package; 3 leads	SOT23
BC858	—	plastic surface mounted package; 3 leads	SOT23

PNP general purpose transistors

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LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BC856		–	–80	V
	BC857		–	–50	V
	BC858		–	–30	V
V _{CEO}	collector-emitter voltage	open base			
	BC856		–	–65	V
	BC857		–	–45	V
	BC858		–	–30	V
V _{EBO}	emitter-base voltage	open collector	–	–5	V
I _C	collector current (DC)		–	–100	mA
I _{CM}	peak collector current		–	–200	mA
I _{BM}	peak base current		–	–200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	250	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board, standard footprint.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	in free air; note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board, standard footprint.

PNP general purpose transistors

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CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

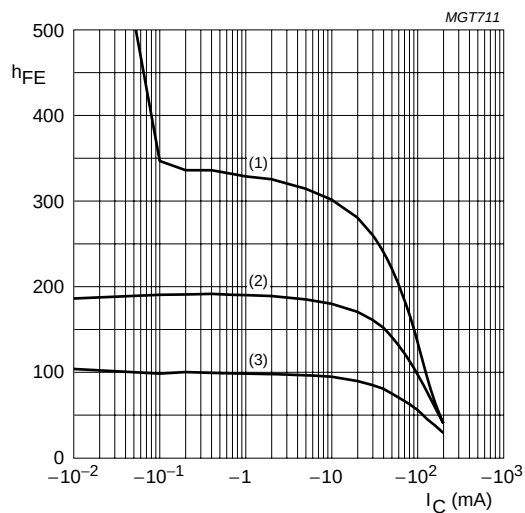
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$V_{CB} = -30\text{ V}; I_E = 0$	–	–1	–15	nA
		$V_{CB} = -30\text{ V}; I_E = 0;$ $T_J = 150\text{ }^{\circ}\text{C}$	–	–	–4	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0$	–	–	–100	nA
h_{FE}	DC current gain	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V}$				
	BC856		125	–	475	
	BC857		125	–	800	
	BC856A; BC857A		125	–	250	
	BC856B; BC857B; BC858B		220	–	475	
	BC857C		420	–	800	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	–	–75	–300	mV
		$I_C = -100\text{ mA}; I_B = -5\text{ mA};$ note 1	–	–250	–650	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	–	–700	–	mV
		$I_C = -100\text{ mA}; I_B = -5\text{ mA};$ note 1	–	–850	–	mV
V_{BE}	base-emitter voltage	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V}$	–600	–650	–750	mV
		$I_C = -10\text{ mA}; V_{CE} = -5\text{ V}$	–	–	–820	mV
C_c	collector capacitance	$V_{CB} = -10\text{ V}; I_E = I_C = 0;$ $f = 1\text{ MHz}$	–	4.5	–	pF
f_T	transition frequency	$V_{CE} = -5\text{ V}; I_C = -10\text{ mA};$ $f = 100\text{ MHz}$	100	–	–	MHz
F	noise figure	$I_C = -200\text{ }\mu\text{A}; V_{CE} = -5\text{ V};$ $R_S = 2\text{ k}\Omega; f = 1\text{ kHz};$ $B = 200\text{ Hz}$	–	2	10	dB

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

PNP general purpose transistors

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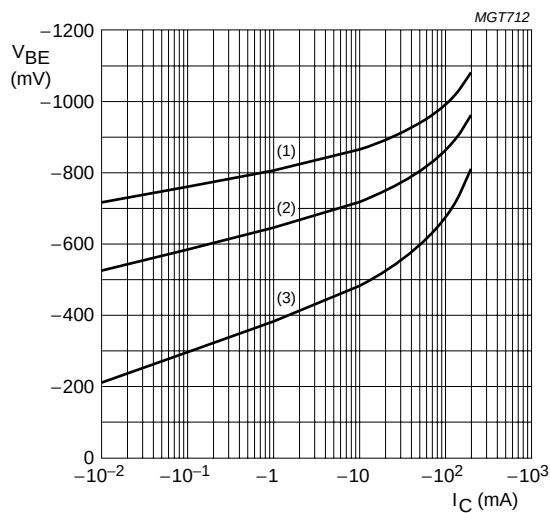
BC857A; $V_{CE} = -5$ V.

(1) $T_{amb} = 150$ °C.

(2) $T_{amb} = 25$ °C.

(3) $T_{amb} = -55$ °C.

Fig.2 DC current gain as a function of collector current; typical values.



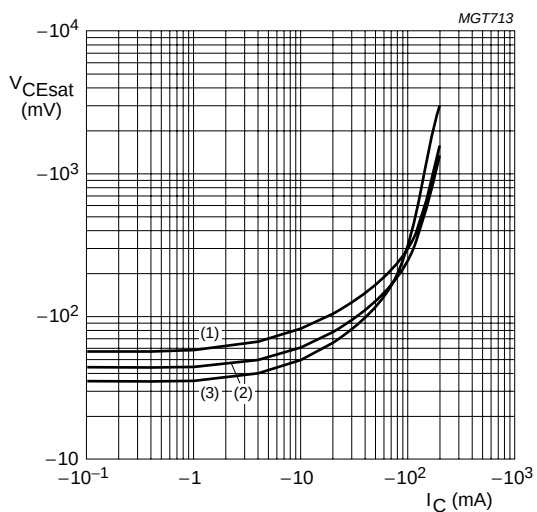
BC857A; $V_{CE} = -5$ V.

(1) $T_{amb} = -55$ °C.

(2) $T_{amb} = 25$ °C.

(3) $T_{amb} = 150$ °C.

Fig.3 Base-emitter voltage as a function of collector current; typical values.



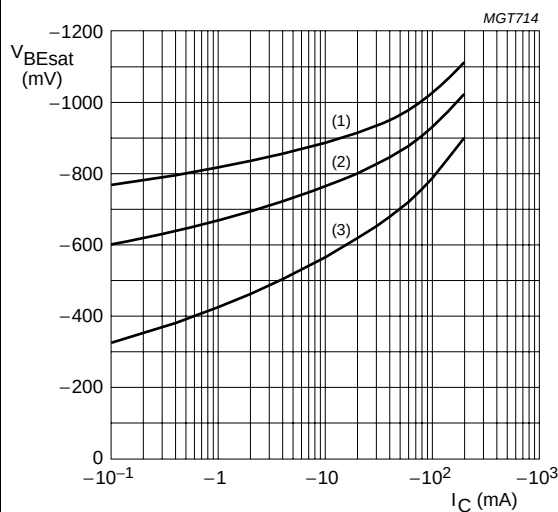
BC857A; $I_C/I_B = 20$.

(1) $T_{amb} = 150$ °C.

(2) $T_{amb} = 25$ °C.

(3) $T_{amb} = -55$ °C.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



BC857A; $I_C/I_B = 20$.

(1) $T_{amb} = -55$ °C.

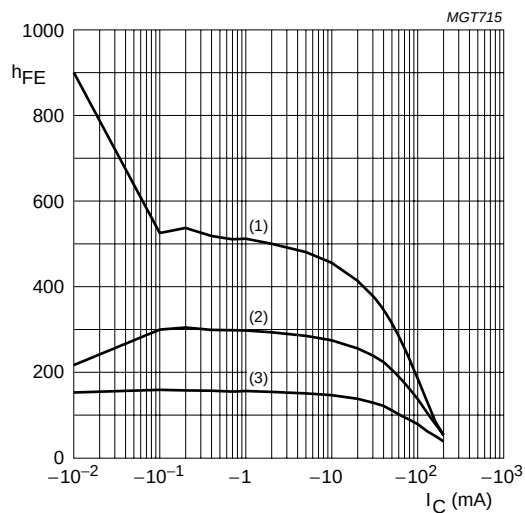
(2) $T_{amb} = 25$ °C.

(3) $T_{amb} = 150$ °C.

Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

PNP general purpose transistors

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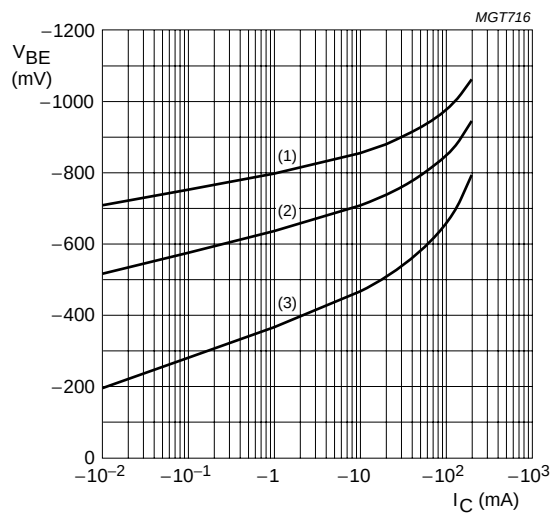
BC857B; $V_{CE} = -5$ V.

(1) $T_{amb} = 150$ °C.

(2) $T_{amb} = 25$ °C.

(3) $T_{amb} = -55$ °C.

Fig.6 DC current gain as a function of collector current; typical values.



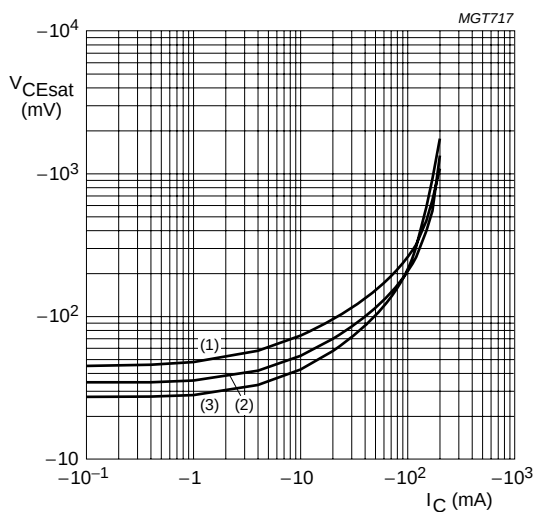
BC857B; $V_{CE} = -5$ V.

(1) $T_{amb} = -55$ °C.

(2) $T_{amb} = 25$ °C.

(3) $T_{amb} = 150$ °C.

Fig.7 Base-emitter voltage as a function of collector current; typical values.



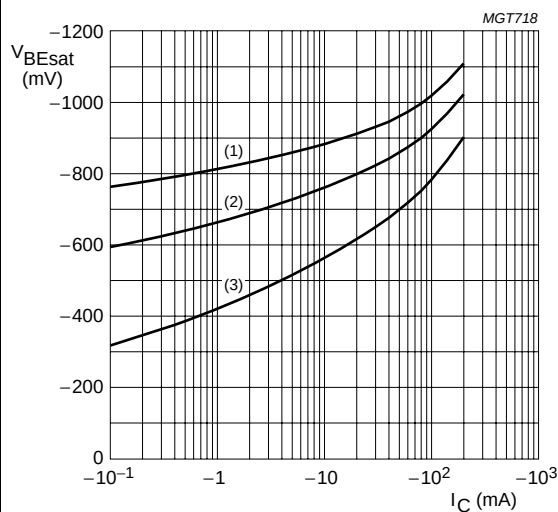
BC857B; $I_C/I_B = 20$.

(1) $T_{amb} = 150$ °C.

(2) $T_{amb} = 25$ °C.

(3) $T_{amb} = -55$ °C.

Fig.8 Collector-emitter saturation voltage as a function of collector current; typical values.



BC857B; $I_C/I_B = 20$.

(1) $T_{amb} = -55$ °C.

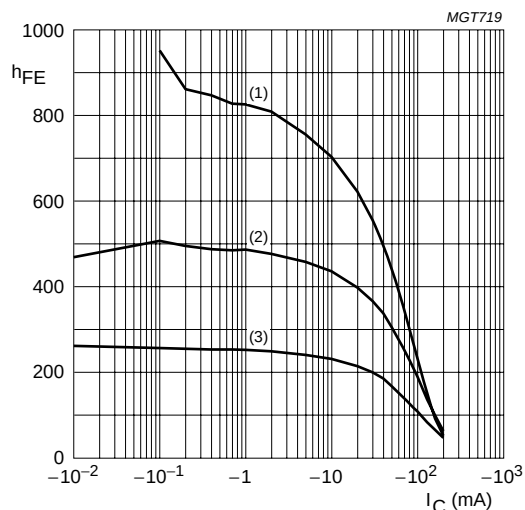
(2) $T_{amb} = 25$ °C.

(3) $T_{amb} = 150$ °C.

Fig.9 Base-emitter saturation voltage as a function of collector current; typical values.

PNP general purpose transistors

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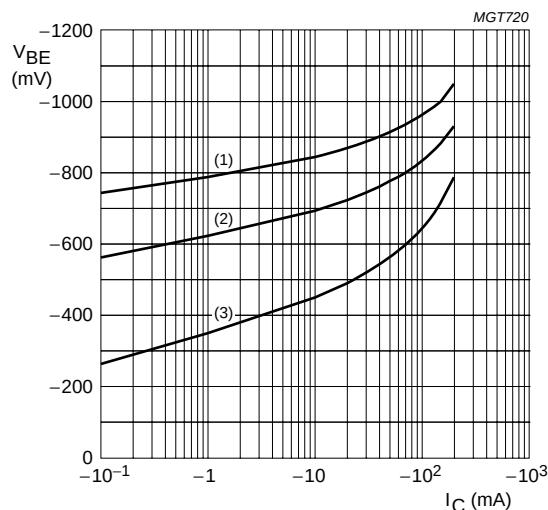
BC857C; $V_{CE} = -5$ V.

(1) $T_{amb} = 150$ °C.

(2) $T_{amb} = 25$ °C.

(3) $T_{amb} = -55$ °C.

Fig.10 DC current gain as a function of collector current; typical values.



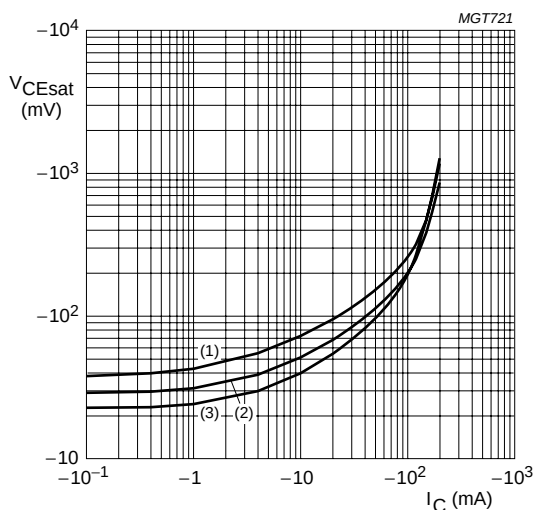
BC857C; $V_{CE} = -5$ V.

(1) $T_{amb} = -55$ °C.

(2) $T_{amb} = 25$ °C.

(3) $T_{amb} = 150$ °C.

Fig.11 Base-emitter voltage as a function of collector current; typical values.



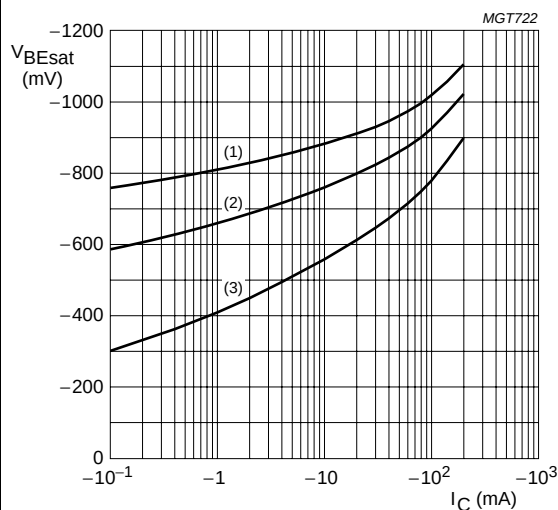
BC857C; $I_C/I_B = 20$.

(1) $T_{amb} = 150$ °C.

(2) $T_{amb} = 25$ °C.

(3) $T_{amb} = -55$ °C.

Fig.12 Collector-emitter saturation voltage as a function of collector current; typical values.



BC857C; $I_C/I_B = 20$.

(1) $T_{amb} = -55$ °C.

(2) $T_{amb} = 25$ °C.

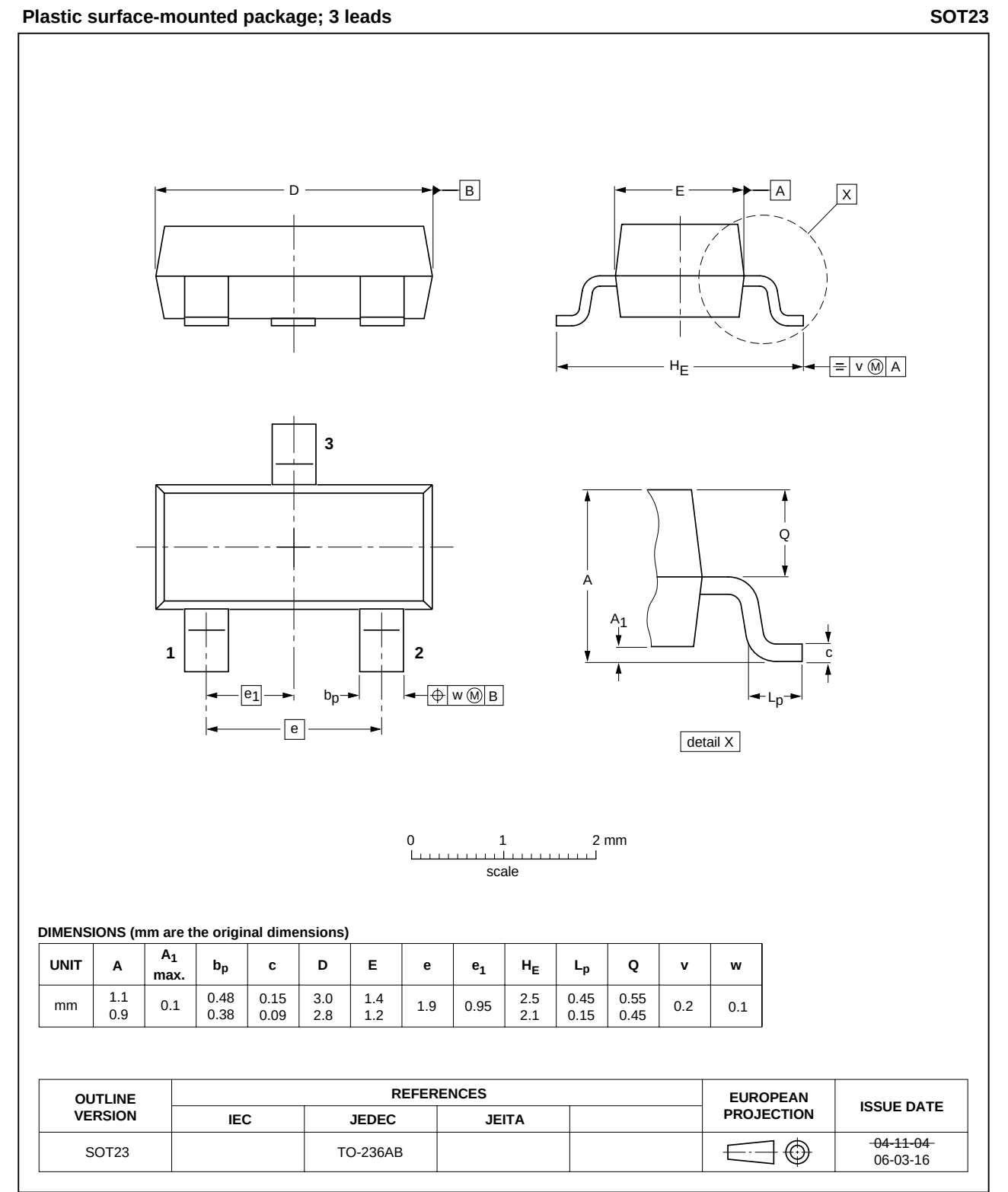
(3) $T_{amb} = 150$ °C.

Fig.13 Base-emitter saturation voltage as a function of collector current; typical values.

PNP general purpose transistors

BC856; BC857; BC858

PACKAGE OUTLINE



PNP general purpose transistors

BC856; BC857; BC858

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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